Electronic Supplementary Information

Phenethylammonium bismuth halides: from single crystals to bulky-organic cation promoted thin-film deposition for potential optoelectronic applications

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Figure S1. Calculated XRD pattern form single crystal characterization and powder XRD pattern of (PEA)₃Bi₂Br₉ and (PEA)₄Bi₂Cl₁₀.



Figure S2. Red colour of the $(PEA)_3Bi_2I_9$ (a) the primary solution and (b) film deposited on FTO .

	(PEA) ₃ Bi ₂ I ₉	(PEA) ₃ Bi ₂ Br ₉	(PEA) ₄ Bi ₂ Cl ₁₀
Empirical formula	C ₂₄ H ₃₆ Bi ₂ I ₉ N ₃	C ₂₄ H ₃₆ Bi ₂ Br ₉ N ₃	$C_{32}H_{48}Bi_2Cl_{10}N_4$
Formula weight	1926.62	1503.71	1261.20
Temperature	190(2) K	190(2) K	190(2) K
Wavelength	0.71073 Å	1.54184 Å	1.54184 Å
Crystal system	Monoclinic	Monoclinic	Monoclinic
Space group	P2 ₁ /n	P2 ₁ /n	P2 ₁ /c
Unit cell dimensions	a=14.5891(4) Å α= 90°	a=14.0039(2) Å α=90°	a=7.9840(3) Å α = 90°
	b=20.4834(4) Å β=113.030(3)°	b=19.5707(2) Å β= 115.492(2)°	b=25.0632(7) Å β= 91.161(3)°
Volumo	c=15.7858(4) Å $\gamma = 90^{\circ}$	$c=15.5528(3) \text{ Å } \gamma = 90^{\circ}$	c=21.8464(6) Å $\gamma = 90^{\circ}$
v olume	4541.57(16) A*	5847.52(10) A ²	4370.7(2) A ²
Z	4	4	4
Density (calculated)	2.948 Mg/m ³	2.596 Mg/m ³	1.917 Mg/m ³
Absorption coefficient	14.514 mm ⁻¹	28.850 mm ⁻¹	21.470 mm ⁻¹
F(000)	3376	2728	2416
Crystal size	3.35 to 25.00°	0.635 x 0.089 x 0.064 mm ³	0.1 x 0.05 x 0.01 mm ³
Theta range for data collection	3.35 to 25.00°.	3.56 to 62.44°.	4.05 to 62.49°.
Index ranges	-17<=h<=17, -24<=k<=24, -18<= <=14	-16<=h<=16, -19<=k<=22, -17<=l<=17	-9<=h<=8, -28<=k<=28, -25<=l<=24
Reflections collected	21493	19929	23916
Independent reflections	7631 [R(int) = 0.0435]	6111 [R(int) = 0.0473]	6951 [R(int) = 0.0522]
Completeness to theta = 25.00°	99.7 %	99.7 %	99.7 %
Absorption correction	Semi-empirical from equivalents	Analytical	Semi-empirical from equivalents
Max. and min. transmission	Max. and min. 1 and 0.2408 transmission		1 and 0.47589
Refinement method	Full-matrix least-squares on F ²	Full-matrix least-squares on F ²	Full-matrix least-squares on F ²
Data / restraints / parameters	7631 / 0 / 346	6111 / 0 / 346	6951 / 30 / 429
Goodness-of-fit on F ²	1.020	1.136	1.018
Final R indices [I>2sigma(I)]	R1 = 0.0340, wR2 = 0.0639	R1 = 0.0375, wR2 = 0.1088	R1 = 0.0332, wR2 = 0.0722

 $\textbf{Table S1}. Crystal data and structure refinement for (PEA)_{3}Bi_{2}I_{9}, (PEA)_{3}Bi_{2}Br_{9} \text{ and } (PEA)_{4}Bi_{2}Cl_{10}$

R indices (all data)	R1 = 0.0463,	R1 = 0.0401,	R1 = 0.0442,
	wR2 = 0.0690	wR2 = 0.1111	wR2 = 0.0781
Largest diff. peak and hole	1.609 and -1.174 e.Å ⁻³	1.301 and -2.042 e.Å ⁻³	1.225 and -0.676 e.Å ⁻³

Table S2. Atomic coordinates (\times 10 ⁴) and equivalent isotropic displacement parameters (Å ² >	10 ³). U(e	eq)
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is defined as one third of the trace of the orthogonalized Uij tensor

		X	Y	Z	U(eq)
	Bi(1)	-0.05359	0.42448	0.3244	0.026
	I(1)	-0.19295	0.08384	0.39218	0.037
(PEA) ₃ Bi ₂ I ₉	I(2)	0.12164	0.07302	0.43655	0.034
	N(1)	2191	0.2751	0.9782	0.064
	C(1)	0.0112	0.1812	0.9456	0.036
	N(2)	0.1120	0.3957	0.6327	0.036
	C(2)	-0.0067	0.1188	0.9789	0.060
	C(3)	0.07910	0.08360	1.00780	0.068
	Bi(1)	0.05771	0.14810	0.66693	0.028
	Br(1)	-0.11709	0.07626	0.55840	0.036
	Br(2)	0.12096	0.06589	0.82055	0.043
(PEA) ₃ Bi ₂ Br ₉	N(1)	-0.28250	0.22500	0.50200	0.049
	C(1)	-0.50070	0.32430	0.53540	0.042
	N(2)	0.34830	0.41640	0.82630	0.040
	C(2)	-0.58530	0.29790	0.54800	0.047
	Bi(1)	0.23481	0.52077	0.65285	0.034
	Cl(1)	0.50890	0.55481	0.58921	0.064
	Cl(2)	0.20930	0.44601	0.57408	0.059
$(PEA)_4Bi_2Cl_{10}$	N(1)	0.76140	0.59970	0.69710	0.074
	C(1)	0.86990	0.74800	0.70230	0.051
	N(2)	0.21100	0.96200	0.94830	0.028
	C(2)	0.78880	0.78560	0.66730	0.050

Table S3.	Bond lengtl	ıs [Å] an	d angles [°] for	$(PEA)_{3}Bi_{2}I_{9},$	(PEA) ₃ Bi ₂ Br ₉ and	$(PEA)_4Bi_2Cl_{10}$.
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	Bond	Angle (°)
	Bi(1)–I(1)	2.9446(6)
	Bi(1)–I(2)	2 2220/0
(PEA)3Bi2I0		2.9060(6)
()52-)	N(1)–C(8)	1.451(11)
	N(2)–C(16)	1.493(9)
	N(3)–C(24)	1.497(9)
	Bi(1)–Br(1)	2.6948(8)
	Bi(1)–Br(2)	2.6944(9)
(PEA) ₃ Bi ₂ Br ₉	N(1)-C(8)	1.475(12)
()0 2)	N(2)–C(16)	1.492(11)
	N(3)–C(24)	1.495(10)
	Bi(1)–Cl (1)	2.7518(19)
	Bi(1)–Cl (2)	2.5493(16)
(PEA) ₄ Bi ₂ Cl ₁₀	N(1)-C(8)	1.494(7)
	N(2)–C(16)	1.494(8)
	N(3)–C(24)	1.476(10)



Figure S3. Calculated electronic band structures and total and partial densities of states (DOS) using Density Functional Theory (DFT) calculations (a) Band structure of (PEA)₃Bi₂Br₉, (b) Band structure of (PEA)₄Bi₂Cl₁₀, DOS of (c) (PEA)₃Bi₂Br₉, (d) DOS of (PEA)₄Bi₂Cl₁₀.

Table S4. Calculated direct band gap at different point of the Brillouin zone and minimum direct and indirect band gap, E_g (eV) of the considered compounds of (PEA)₃Bi₂Br₉ and (PEA)₄Bi₂Cl₁₀.

Compounds	Direct				Indirect	
	Γ (0, 0, 0)	F (0, 0.5,	Q (0, 0.5,	Z (0, 0,	Mi	nimum
		0)	0.5)	0.5)		
(PEA) ₃ Bi ₂ Br ₉	2.64	2.64	2.65	2.63	2.63	2.58
$(PEA)_4Bi_2Cl_{10}$	3.37	3.38	3.5	3.49	3.37	3.33



Figure S4. SEM images of $A_3Bi_2I_9$ film deposited on FTO with different organic cations of (a) Formamidium (CH₅N₂, FA), (b) Methylamonium (CH₆N, MA), (c) n-Butylammonium (C₄H₁₂N, BA), (d) Phenethylammonium (C₈H₁₂N, PEA).

Table S5. Various device parameters of the best-performing devices with $MA_3Bi_2I_9$ and (PEA)_3Bi_2I_9 as the active layer in FTO / C-TiO_2 / Perovskite derivative / P3HT /Au structure.

Active Layer	J _{sc} (mA/cm ²)	V _{oc} (V)	FF	PCE (%)
MA ₃ Bi ₂ I ₉	0.24	0.43	0.42	0.043
(PEA)3Bi2I9	0.39	0.49	0.45	0.086



Figure S5. (a) J–V curve of the best performing devices with MA₃Bi₂I₉ and (PEA)₃Bi₂I₉ as the active layer with FTO / C-TiO₂ / Perovskite derivative / P3HT/ Au structure. Statistical photovoltaic parameters of 13 devices with FTO / C-TiO₂ / bismuth organohalides / P3HT/ Au structure, (b) J_{sc} , (c) V_{oc} , (d) FF, and (e) PCE.



Figure S6. Statistical distribution of (a) J_{sc} , (b) V_{oc} , (c) FF and (d) PCE for 24 devices based on the MA₃Bi₂I₉ and (PEA)₃Bi₂I₉ with FTO / C-TiO₂ / M-TiO₂ / bismuth organohalides / P3HT / Au structure.



Figure S7. EQE results for the device with FTO / $C-TiO_2$ / $M-TiO_2$ / (PEA)₃Bi₂I₉ / P3HT / Au structure.



Figure S8. J–V curve of the device with the structure of $FTO / C-TiO_2 / M-TiO_2 / P3HT / Au$.



Figure S9. J–V curves of a $(PEA)_3Bi_2I_9$ device scanned from forward and reverse bias.

Table S6. Photovoltaic properties of $(PEA)_3Bi_2I_9$ based solar cell with variousdurations of storage in ambient air.

Time	J _{sc} (mA/cm ²)	V _{oc} (V)	FF	PCE (%)
Day 1	0.521	0.552	0.459	0.131
Day 4	0.812	0.557	0.46	0.183
Day 8	0.834	0.556	0.469	0.193
Day 10	0.814	0.590	0.45	0.216
Day 15	0.770	0.560	0.442	0.191
Day 20	0.740	0.559	0.436	0.18



Figure S10. Efficiency of the $(PEA)_3Bi_2I_9$ device with the structure of FTO / C-TiO₂ / M-TiO₂ / (PEA)₃Bi₂I₉ / Au upon storage in air for 20 days.